

Isc N-Channel MOSFET Transistor

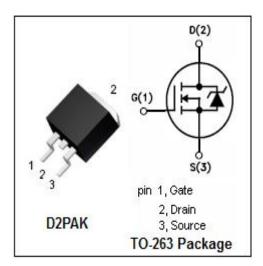
IRF3415S

• FEATURES

- · With To-263(D2PAK) package
- · Low input capacitance and gate charge
- · Low gate input resistance
- · 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



Switching applications

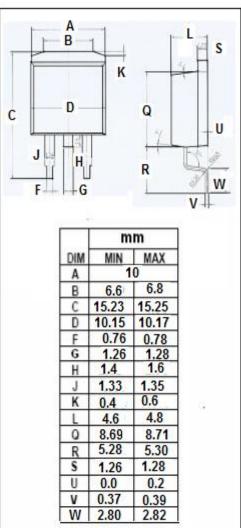


• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

| SYMBOL | PARAMETER | VALUE | UNIT |
|------------------|-------------------------------------------|----------|----------------------|
| V_{DSS} | Drain-Source Voltage | 150 | V |
| V _{GSS} | Gate-Source Voltage | ±20 | V |
| I _D | Drain Current-ContinuousTc=25℃ Tc=100℃ | 43 30 | А |
| I _{DM} | Drain Current-Single Pulsed | 150 | А |
| P _D | Total Dissipation @Tc=25℃ | 200 | W |
| T _{ch} | Max. Operating Junction Temperature | 175 | $^{\circ}\mathbb{C}$ |
| T _{stg} | Storage Temperature | -55~175 | °C |

• THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | | UNIT | |
|-----------|---------------------------------------------|------|------|--|
| Rth(ch-c) | Channel-to-case thermal resistance | 0.75 | °C/W | |
| Rth(ch-a) | a) Channel-to-ambient thermal resistance 40 | | °C/W | |



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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | ТҮР | MAX | UNIT |
|---------------------|--------------------------------|-------------------------------------------------------------------------------------------------------------|-----|-----|-----------|------|
| BV _{DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V; I _D =0.25mA | 150 | | | V |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} =V _{GS} ; I _D =0.25mA | 2.0 | | 4.0 | V |
| R _{DS(on)} | Drain-Source On-Resistance | V _{GS} = 10V; I _D =22A | | | 42 | mΩ |
| I _{GSS} | Gate-Source Leakage Current | V _{GS} = ±20V;V _{DS} =0V | | | ±0.1 | μА |
| I _{DSS} | Drain-Source Leakage Current | V _{DS} =150V; V _{GS} = 0V;Tj=25°C V _{DS} =120V; V _{GS} = 0V;Tj=125°C | | | 25 250 | μА |
| V _{SDF} | Diode forward voltage | I _{SD} =22A, V _{GS} = 0 V | | | 1.3 | V |



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